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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	37
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.8V
Data Converters	A/D 12bit SAR; D/A 12bit
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-TQFP
Supplier Device Package	48-TQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32tg11b320f128gq48-ar

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Max load current	I_{LOAD_MAX}	Low noise (LN) mode, Heavy Drive[2], T ≤ 85 °C	—	—	200	mA
		Low noise (LN) mode, Heavy Drive[2], T > 85 °C	—	—	100	mA
		Low noise (LN) mode, Medium Drive[2]	—	—	100	mA
		Low noise (LN) mode, Light Drive[2]	—	—	50	mA
		Low power (LP) mode, LPCMPBIASEMxx[3] = 0	—	—	75	µA
		Low power (LP) mode, LPCMPBIASEMxx[3] = 3	—	—	10	mA
DCDC nominal output capacitor[5]	C_{DCDC}	25% tolerance	1	4.7	4.7	µF
DCDC nominal output inductor	L_{DCDC}	20% tolerance	4.7	4.7	4.7	µH
Resistance in Bypass mode	R_{BYP}		—	1.2	TBD	Ω

Note:

1. Due to internal dropout, the DC-DC output will never be able to reach its input voltage, $V_{VREGVDD}$.
2. Drive levels are defined by configuration of the PFETCNT and NFETCNT registers. Light Drive: PFETCNT=NFETCNT=3; Medium Drive: PFETCNT=NFETCNT=7; Heavy Drive: PFETCNT=NFETCNT=15.
3. LPCMPBIASEMxx refers to either LPCMPBIASEM234H in the EMU_DCDCMISCCTRL register or LPCMPBIASEM01 in the EMU_DCDCLOEM01CFG register, depending on the energy mode.
4. LP mode controller is a hysteretic controller that maintains the output voltage within the specified limits.
5. Output voltage under/over-shoot and regulation are specified with C_{DCDC} 4.7 µF. Different settings for DCDCLNCOMPCTRL must be used if C_{DCDC} is lower than 4.7 µF. See Application Note AN0948 for details.

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Current consumption in EM0 mode with all peripherals disabled and voltage scaling enabled, DCDC in Low Noise CCM mode[1]	$I_{ACTIVE\_CCM\_VS}$	19 MHz HFRCO, CPU running while loop from flash	—	81	—	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	1147	—	µA/MHz
Current consumption in EM0 mode with all peripherals disabled and voltage scaling enabled, DCDC in LP mode[3]	$I_{ACTIVE\_LPM\_VS}$	19 MHz HFRCO, CPU running while loop from flash	—	30	—	µA/MHz
		1 MHz HFRCO, CPU running while loop from flash	—	144	—	µA/MHz
Current consumption in EM1 mode with all peripherals disabled, DCDC in Low Noise DCM mode[2]	I_{EM1_DCM}	48 MHz crystal	—	31	—	µA/MHz
		48 MHz HFRCO	—	30	—	µA/MHz
		32 MHz HFRCO	—	36	—	µA/MHz
		26 MHz HFRCO	—	41	—	µA/MHz
		16 MHz HFRCO	—	54	—	µA/MHz
		1 MHz HFRCO	—	581	—	µA/MHz
Current consumption in EM1 mode with all peripherals disabled, DCDC in Low Power mode[3]	I_{EM1_LPM}	32 MHz HFRCO	—	25	—	µA/MHz
		26 MHz HFRCO	—	26	—	µA/MHz
		16 MHz HFRCO	—	29	—	µA/MHz
		1 MHz HFRCO	—	153	—	µA/MHz
Current consumption in EM1 mode with all peripherals disabled and voltage scaling enabled, DCDC in Low Noise DCM mode[2]	$I_{EM1\_DCM\_VS}$	19 MHz HFRCO	—	46	—	µA/MHz
		1 MHz HFRCO	—	573	—	µA/MHz
Current consumption in EM1 mode with all peripherals disabled and voltage scaling enabled. DCDC in LP mode[3]	$I_{EM1\_LPM\_VS}$	19 MHz HFRCO	—	25	—	µA/MHz
		1 MHz HFRCO	—	140	—	µA/MHz
Current consumption in EM2 mode, with voltage scaling enabled, DCDC in LP mode[3]	I_{EM2_VS}	Full 32 kB RAM retention and RTCC running from LFXO	—	1.26	—	µA
		Full 32 kB RAM retention and RTCC running from LFRCO	—	1.54	—	µA
		8 kB (1 bank) RAM retention and RTCC running from LFRCO[5]	—	1.30	—	µA
Current consumption in EM3 mode, with voltage scaling enabled	I_{EM3_VS}	Full 32 kB RAM retention and CRYOTIMER running from ULFRCO	—	0.93	—	µA
Current consumption in EM4H mode, with voltage scaling enabled	I_{EM4H_VS}	128 byte RAM retention, RTCC running from LFXO	—	0.78	—	µA
		128 byte RAM retention, CRYOTIMER running from ULFRCO	—	0.50	—	µA
		128 byte RAM retention, no RTCC	—	0.50	—	µA
Current consumption in EM4S mode	I_{EM4S}	No RAM retention, no RTCC	—	0.06	—	µA

4.1.10 Flash Memory Characteristics[5]

Table 4.17. Flash Memory Characteristics[5]

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Flash erase cycles before failure	EC_{FLASH}		10000	—	—	cycles
Flash data retention	RET_{FLASH}	T ≤ 85 °C	10	—	—	years
		T ≤ 125 °C	10	—	—	years
Word (32-bit) programming time	t_{W_PROG}	Burst write, 128 words, average time per word	20	26	32	µs
		Single word	59	68	83	µs
Page erase time[4]	t_{PERASE}		20	27	35	ms
Mass erase time[1]	t_{MERASE}		20	27	35	ms
Device erase time[2 3]	t_{DERASE}	T ≤ 85 °C	—	54	70	ms
		T ≤ 125 °C	—	54	75	ms
Erase current[6]	I_{ERASE}	Page Erase	—	—	1.7	mA
		Mass or Device Erase	—	—	2.0	mA
Write current[6]	I_{WRITE}		—	—	3.5	mA
Supply voltage during flash erase and write	V_{FLASH}		1.62	—	3.6	V

Note:

1. Mass erase is issued by the CPU and erases all flash.
2. Device erase is issued over the AAP interface and erases all flash, SRAM, the Lock Bit (LB) page, and the User data page Lock Word (ULW).
3. From setting the DEVICEERASE bit in AAP_CMD to 1 until the ERASEBUSY bit in AAP_STATUS is cleared to 0. Internal setup and hold times for flash control signals are included.
4. From setting the ERASEPAGE bit in MSC_WRITECMD to 1 until the BUSY bit in MSC_STATUS is cleared to 0. Internal setup and hold times for flash control signals are included.
5. Flash data retention information is published in the Quarterly Quality and Reliability Report.
6. Measured at 25 °C.

4.1.13 Analog to Digital Converter (ADC)

Specified at 1 Msps, ADCCLK = 16 MHz, BIASPROG = 0, GPBIASACC = 0, unless otherwise indicated.

Table 4.20. Analog to Digital Converter (ADC)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Resolution	$V_{RESOLUTION}$		6	—	12	Bits
Input voltage range[5]	V_{ADCIN}	Single ended	—	—	V_{FS}	V
		Differential	$-V_{FS}/2$	—	$V_{FS}/2$	V
Input range of external reference voltage, single ended and differential	$V_{ADCREFIN\_P}$		1	—	V_{AVDD}	V
Power supply rejection[2]	$PSRR_{ADC}$	At DC	—	80	—	dB
Analog input common mode rejection ratio	$CMRR_{ADC}$	At DC	—	80	—	dB
Current from all supplies, using internal reference buffer. Continous operation. WARMUPMODE[4] = KEEPADCWARM	$I_{ADC\_CONTINOUS\_LP}$	1 Msps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 1 [3]	—	270	TBD	µA
		250 ksps / 4 MHz ADCCLK, BIASPROG = 6, GPBIASACC = 1 [3]	—	125	—	µA
		62.5 ksps / 1 MHz ADCCLK, BIASPROG = 15, GPBIASACC = 1 [3]	—	80	—	µA
Current from all supplies, using internal reference buffer. Duty-cycled operation. WARMUPMODE[4] = NORMAL	$I_{ADC\_NORMAL\_LP}$	35 ksps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 1 [3]	—	45	—	µA
		5 ksps / 16 MHz ADCCLK BIASPROG = 0, GPBIASACC = 1 [3]	—	8	—	µA
Current from all supplies, using internal reference buffer. Duty-cycled operation. AWARMUPMODE[4] = KEEPINSTANDBY or KEEPINSLOWACC	$I_{ADC\_STANDBY\_LP}$	125 ksps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 1 [3]	—	105	—	µA
		35 ksps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 1 [3]	—	70	—	µA
Current from all supplies, using internal reference buffer. Continous operation. WARMUPMODE[4] = KEEPADCWARM	$I_{ADC\_CONTINOUS\_HP}$	1 Msps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 0 [3]	—	325	—	µA
		250 ksps / 4 MHz ADCCLK, BIASPROG = 6, GPBIASACC = 0 [3]	—	175	—	µA
		62.5 ksps / 1 MHz ADCCLK, BIASPROG = 15, GPBIASACC = 0 [3]	—	125	—	µA
Current from all supplies, using internal reference buffer. Duty-cycled operation. WARMUPMODE[4] = NORMAL	$I_{ADC\_NORMAL\_HP}$	35 ksps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 0 [3]	—	85	—	µA
		5 ksps / 16 MHz ADCCLK BIASPROG = 0, GPBIASACC = 0 [3]	—	16	—	µA
Current from all supplies, using internal reference buffer. Duty-cycled operation. AWARMUPMODE[4] = KEEPINSTANDBY or KEEPINSLOWACC	$I_{ADC\_STANDBY\_HP}$	125 ksps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 0 [3]	—	160	—	µA
		35 ksps / 16 MHz ADCCLK, BIASPROG = 0, GPBIASACC = 0 [3]	—	125	—	µA
Current from HFPERCLK	I_{ADC_CLK}	HFPERCLK = 16 MHz	—	166	—	µA

4.1.17 Operational Amplifier (OPAMP)

Unless otherwise indicated, specified conditions are: Non-inverting input configuration, VDD = 3.3 V, DRIVESTRENGTH = 2, MAINOUTEN = 1, C_{LOAD} = 75 pF with OUTSCALE = 0, or C_{LOAD} = 37.5 pF with OUTSCALE = 1. Unit gain buffer and 3X-gain connection as specified in table footnotes[8] [1].

Table 4.24. Operational Amplifier (OPAMP)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Supply voltage (from AVDD)	V_{OPA}	HCMDIS = 0, Rail-to-rail input range	2	—	3.8	V
		HCMDIS = 1	1.62	—	3.8	V
Input voltage	V_{IN}	HCMDIS = 0, Rail-to-rail input range	V_{VSS}	—	V_{OPA}	V
		HCMDIS = 1	V_{VSS}	—	V_{OPA}-1.2	V
Input impedance	R_{IN}		100	—	—	MΩ
Output voltage	V_{OUT}		V_{VSS}	—	V_{OPA}	V
Load capacitance[2]	C_{LOAD}	OUTSCALE = 0	—	—	75	pF
		OUTSCALE = 1	—	—	37.5	pF
Output impedance	R_{OUT}	DRIVESTRENGTH = 2 or 3, 0.4 V ≤ V_{OUT} ≤ V_{OPA} - 0.4 V, -8 mA < I_{OUT} < 8 mA, Buffer connection, Full supply range	—	0.25	—	Ω
		DRIVESTRENGTH = 0 or 1, 0.4 V ≤ V_{OUT} ≤ V_{OPA} - 0.4 V, -400 µA < I_{OUT} < 400 µA, Buffer connection, Full supply range	—	0.6	—	Ω
		DRIVESTRENGTH = 2 or 3, 0.1 V ≤ V_{OUT} ≤ V_{OPA} - 0.1 V, -2 mA < I_{OUT} < 2 mA, Buffer connection, Full supply range	—	0.4	—	Ω
		DRIVESTRENGTH = 0 or 1, 0.1 V ≤ V_{OUT} ≤ V_{OPA} - 0.1 V, -100 µA < I_{OUT} < 100 µA, Buffer connection, Full supply range	—	1	—	Ω
Internal closed-loop gain	G_{CL}	Buffer connection	TBD	1	TBD	-
		3x Gain connection	TBD	2.99	TBD	-
		16x Gain connection	TBD	15.7	TBD	-
Active current[4]	I_{OPA}	DRIVESTRENGTH = 3, OUTSCALE = 0	—	580	—	µA
		DRIVESTRENGTH = 2, OUTSCALE = 0	—	176	—	µA
		DRIVESTRENGTH = 1, OUTSCALE = 0	—	13	—	µA
		DRIVESTRENGTH = 0, OUTSCALE = 0	—	4.7	—	µA

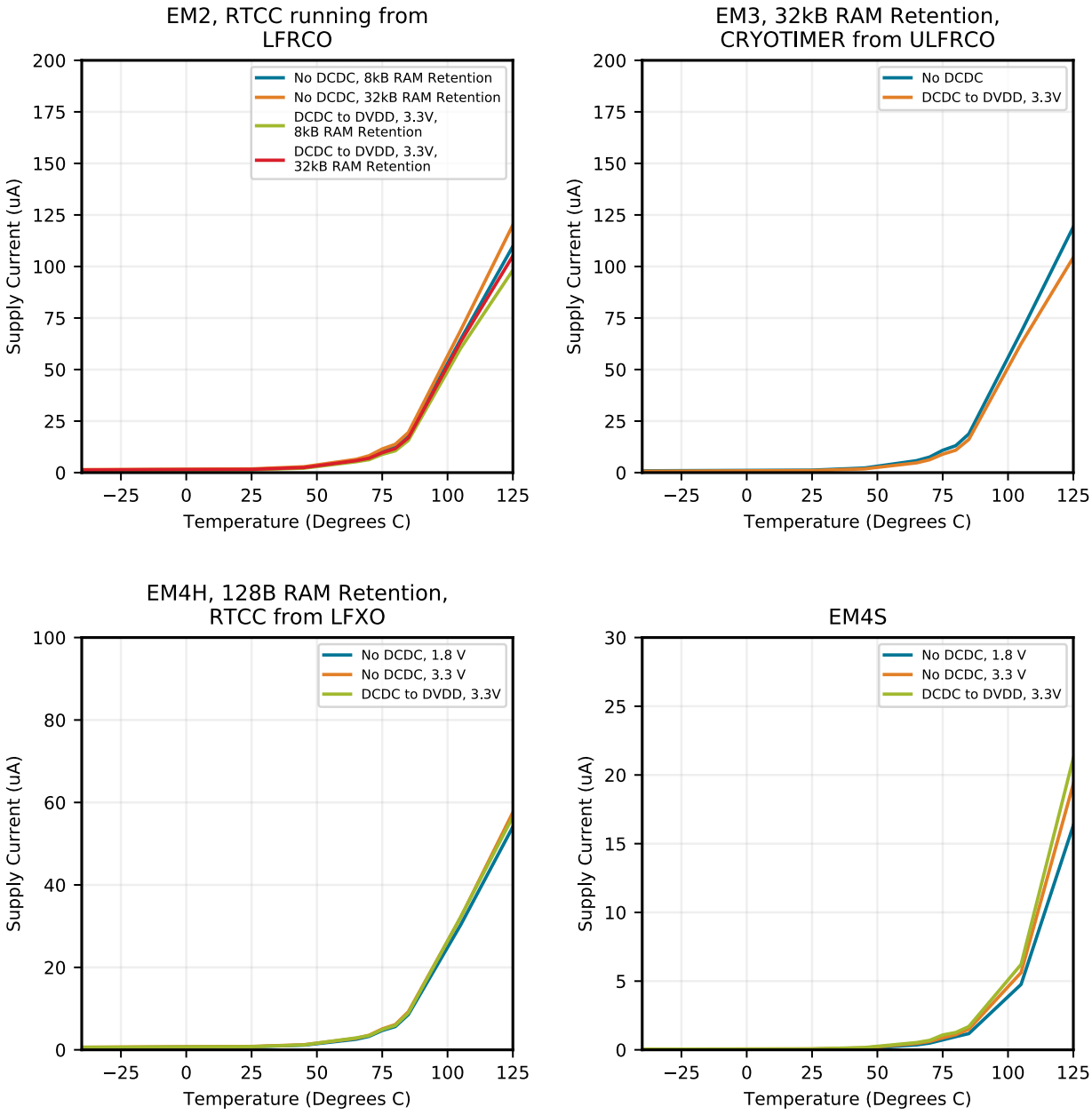

Figure 4.5. EM2, EM3, EM4H and EM4S Typical Supply Current vs. Temperature

4.2.2 DC-DC Converter

Default test conditions: CCM mode, LDCDC = 4.7 µH, CDCDC = 4.7 µF, VDCDC_I = 3.3 V, VDCDC_O = 1.8 V, FDCDC_LN = 7 MHz

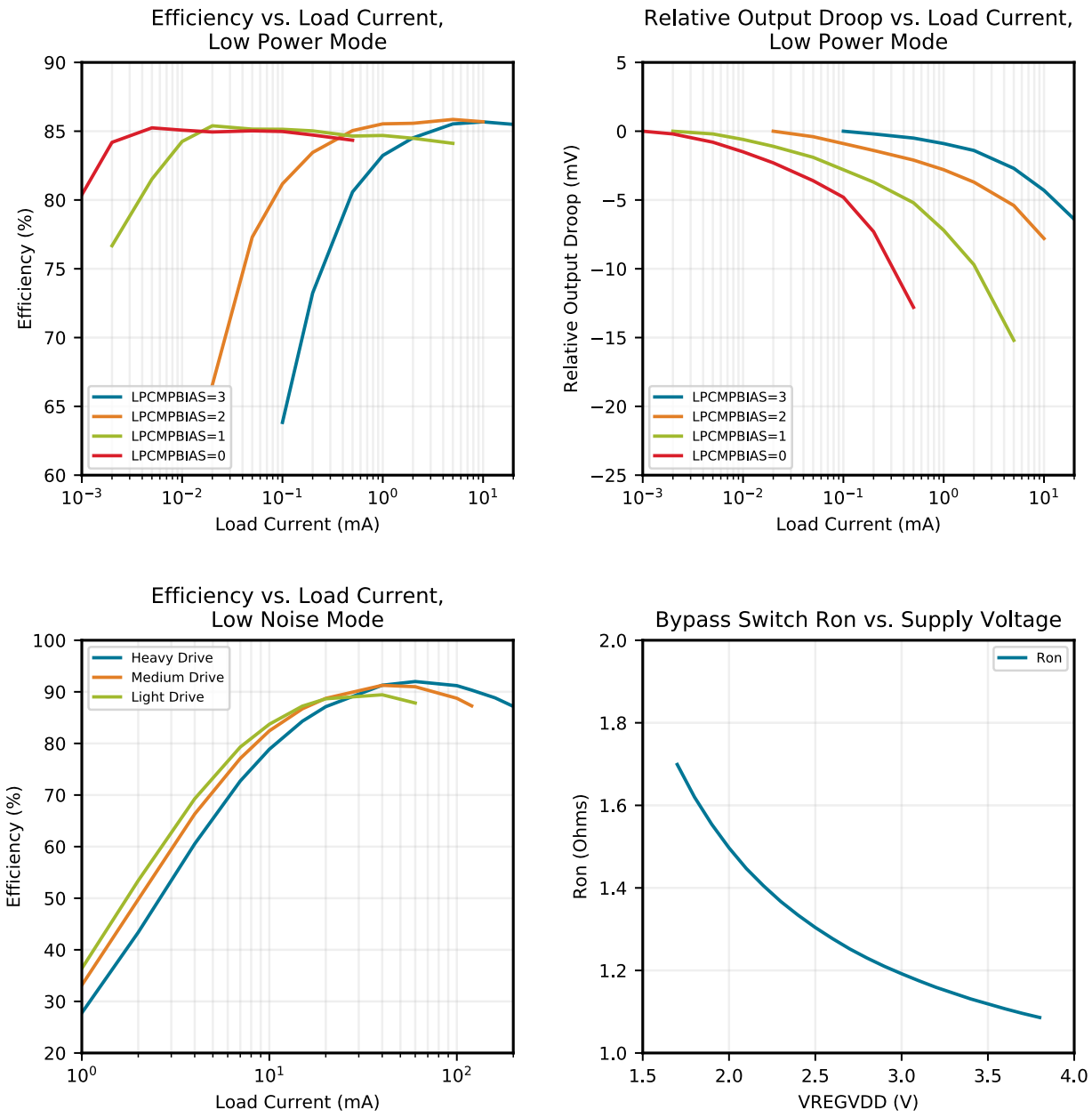

Figure 4.8. DC-DC Converter Typical Performance Characteristics

5.7 EFM32TG11B3xx in QFN64 Device Pinout

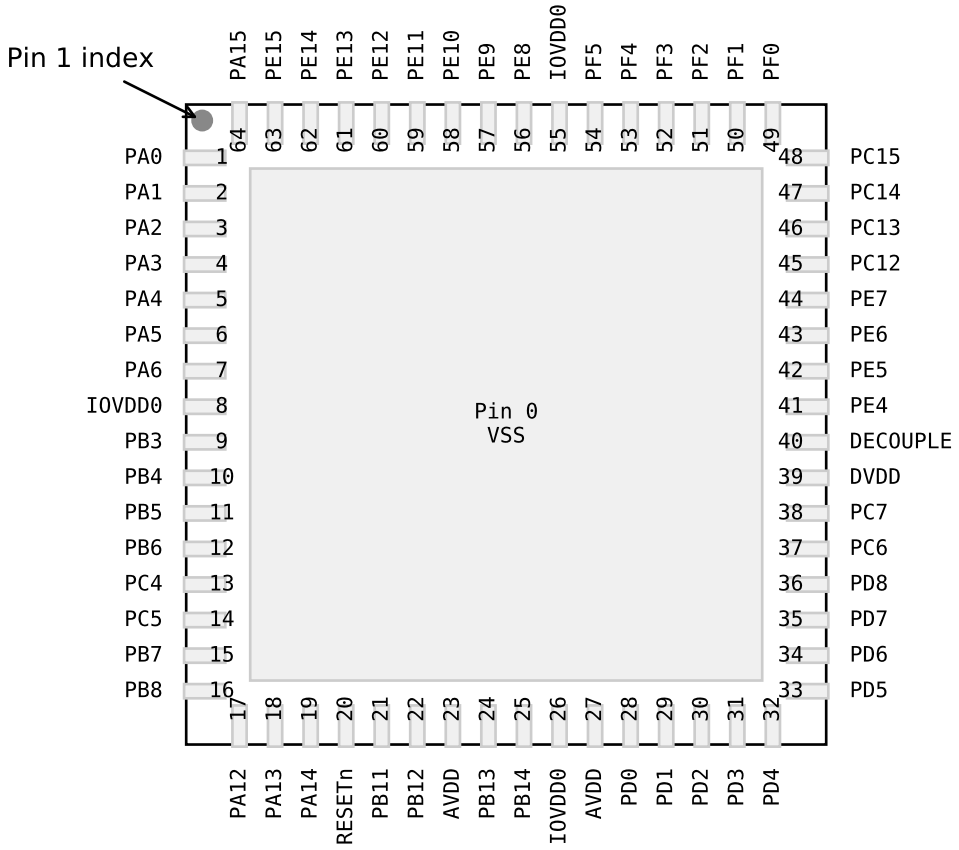

Figure 5.7. EFM32TG11B3xx in QFN64 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.14 GPIO Functionality Table or 5.15 Alternate Functionality Overview.

Table 5.7. EFM32TG11B3xx in QFN64 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
VREGVSS	0	Voltage regulator VSS	PA0	1	GPIO
PA1	2	GPIO	PA2	3	GPIO
PA3	4	GPIO	PA4	5	GPIO
PA5	6	GPIO	PA6	7	GPIO
IOVDD0	8 26 55	Digital IO power supply 0.	PB3	9	GPIO
PB4	10	GPIO	PB5	11	GPIO

5.10 EFM32TG11B3xx in QFP48 Device Pinout

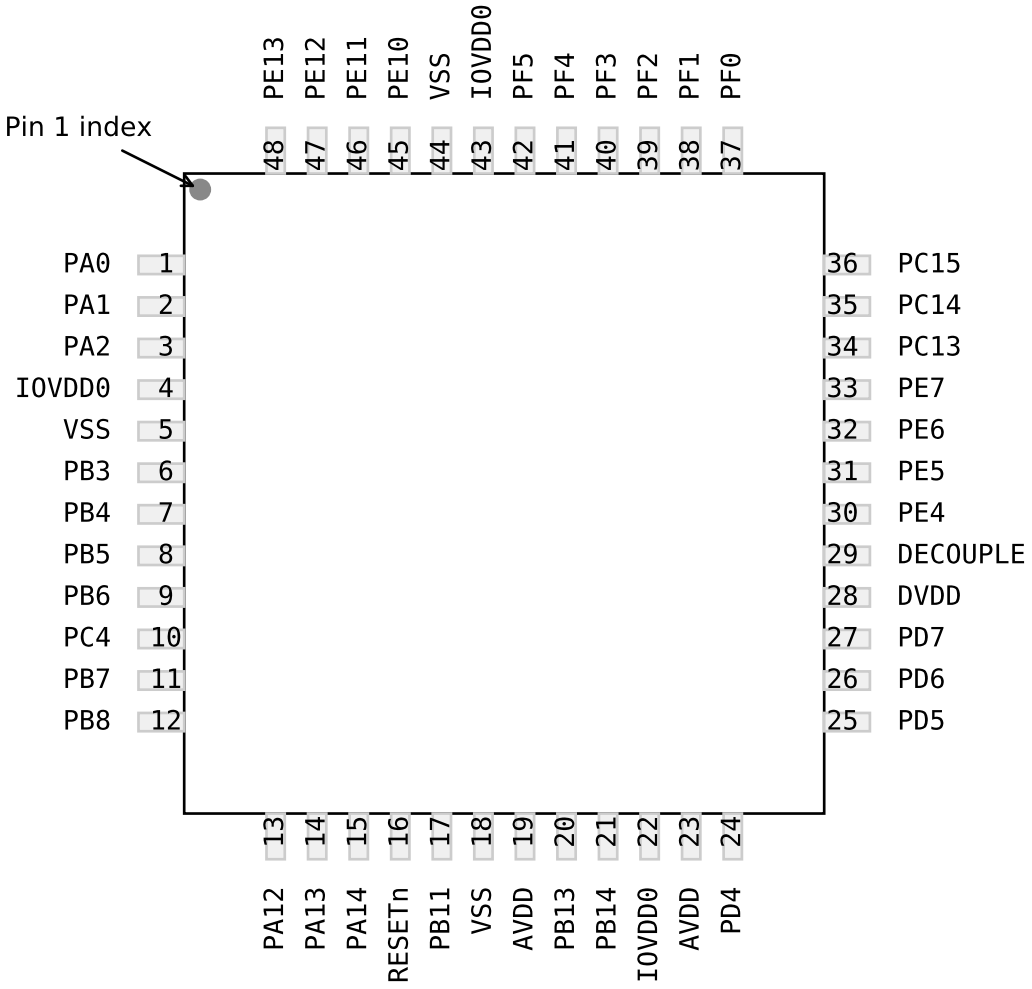

Figure 5.10. EFM32TG11B3xx in QFP48 Device Pinout

The following table provides package pin connections and general descriptions of pin functionality. For detailed information on the supported features for each GPIO pin, see 5.14 GPIO Functionality Table or 5.15 Alternate Functionality Overview.

Table 5.10. EFM32TG11B3xx in QFP48 Device Pinout

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA0	1	GPIO	PA1	2	GPIO
PA2	3	GPIO	IOVDD0	4 22 43	Digital IO power supply 0.
VSS	5 18 44	Ground	PB3	6	GPIO
PB4	7	GPIO	PB5	8	GPIO
PB6	9	GPIO	PC4	10	GPIO

Pin Name	Pin(s)	Description	Pin Name	Pin(s)	Description
PA14	8	GPIO	RESETn	9	Reset input, active low. To apply an external reset source to this pin, it is required to only drive this pin low during reset, and let the internal pull-up ensure that reset is released.
PB11	10	GPIO	AVDD	11	Analog power supply.
PB13	12	GPIO	PB14	13	GPIO
PD4	15	GPIO	PD5	16	GPIO
PD6	17	GPIO	PD7	18	GPIO
VREGSW	20	DCDC regulator switching node	VREGVDD	21	Voltage regulator VDD input
DVDD	22	Digital power supply.	DECOUPLE	23	Decouple output for on-chip voltage regulator. An external decoupling capacitor is required at this pin.
PE4	24	GPIO	PE5	25	GPIO
PC15	26	GPIO (5V)	PF0	27	GPIO (5V)
PF1	28	GPIO (5V)	PF2	29	GPIO
PE11	31	GPIO	PE12	32	GPIO

Note:

1. GPIO with 5V tolerance are indicated by (5V).

GPIO Name	Pin Alternate Functionality / Description			
	Analog	Timers	Communication	Other
PD5	BUSADC0Y BUSADC0X OPA2_OUT	WTIM0_CDTI1 #4 WTIM1_CC3 #1	US1_RTS #1 U0_CTS #5 LEU0_RX #0 I2C1_SCL #3	
PD6	BUSADC0Y BUSADC0X ADC0_EXTP VDAC0_EXT OPA1_P	TIM1_CC0 #4 WTIM0_CDTI2 #4 WTIM1_CC0 #2 LE-TIM0_OUT0 #0 PCNT0_S0IN #3	US0_RTS #5 US1_RX #2 US2_CTS #5 US3_CTS #2 U0_RTS #5 I2C0_SDA #1	CMU_CLK2 #2 LES_AL-TEX0 PRS_CH5 #2 ACMP0_O #2
PD7	BUSADC0Y BUSADC0X ADC0_EXTN OPA1_N	TIM1_CC1 #4 WTIM1_CC1 #2 LE-TIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 US3_CLK #1 U0_TX #6 I2C0_SCL #1	CMU_CLK0 #2 LES_AL-TEX1 ACMP1_O #2
PD8	BU_VIN	WTIM1_CC2 #2	US2_RTS #5	CMU_CLK1 #1
PC6	BUSACMP0Y BU-SACMP0X OPA3_P LCD_SEG32	WTIM1_CC3 #2	US0_RTS #2 US1_CTS #3 I2C0_SDA #2	LES_CH6
PC7	BUSACMP0Y BU-SACMP0X OPA3_N LCD_SEG33	WTIM1_CC0 #3	US0_CTS #2 US1_RTS #3 I2C0_SCL #2	LES_CH7
PE4	BUSDY BUSCX LCD_COM0	WTIM0_CC0 #0 WTIM1_CC1 #4	US0_CS #1 US1_CS #5 US3_CS #1 U0_RX #6 I2C0_SDA #7	
PE5	BUSCY BUSDX LCD_COM1	WTIM0_CC1 #0 WTIM1_CC2 #4	US0_CLK #1 US1_CLK #6 US3_CTS #1 I2C0_SCL #7	
PE6	BUSDY BUSCX LCD_COM2	WTIM0_CC2 #0 WTIM1_CC3 #4	US0_RX #1 US3_TX #1	PRS_CH6 #2
PE7	BUSCY BUSDX LCD_COM3	WTIM1_CC0 #5	US0_TX #1 US3_RX #1	PRS_CH7 #2
PC8	BUSACMP1Y BU-SACMP1X LCD_SEG34		US0_CS #2	LES_CH8 PRS_CH4 #0
PC9	BUSACMP1Y BU-SACMP1X LCD_SEG35		US0_CLK #2	LES_CH9 PRS_CH5 #0 GPIO_EM4WU2
PC10	BUSACMP1Y BU-SACMP1X		US0_RX #2	LES_CH10
PC11	BUSACMP1Y BU-SACMP1X		US0_TX #2 I2C1_SDA #4	LES_CH11
PC12	VDAC0_OUT1ALT / OPA1_OUTALT #0 BU-SACMP1Y BUSACMP1X	TIM1_CC3 #0	US0_RTS #3 US1_CTS #4 US2_CTS #4 U0_RTS #3	CMU_CLK0 #1 LES_CH12
PC13	VDAC0_OUT1ALT / OPA1_OUTALT #1 BU-SACMP1Y BUSACMP1X	TIM0_CDTI0 #1 TIM1_CC0 #0 TIM1_CC2 #4 PCNT0_S0IN #0	US0_CTS #3 US1_RTS #4 US2_RTS #4 U0_CTS #3	LES_CH13
PC14	VDAC0_OUT1ALT / OPA1_OUTALT #2 BU-SACMP1Y BUSACMP1X	TIM0_CDTI1 #1 TIM1_CC1 #0 TIM1_CC3 #4 LETIM0_OUT0 #5 PCNT0_S1IN #0	US0_CS #3 US1_CS #3 US2_RTS #3 US3_CS #2 U0_TX #3 LEU0_TX #5	LES_CH14 PRS_CH0 #2

GPIO Name	Pin Alternate Functionality / Description			
	Analog	Timers	Communication	Other
PC15	VDAC0_OUT1ALT / OPA1_OUTALT #3 BU-SACMP1Y BUSACMP1X	TIM0_CDTI2 #1 TIM1_CC2 #0 WTIM0_CC0 #4 LE-TIM0_OUT1 #5	US0_CLK #3 US1_CLK #3 US3_RTS #3 U0_RX #3 LEU0_RX #5	LES_CH15 PRS_CH1 #2
PF0	BUSDY BUSCX	TIM0_CC0 #4 WTIM0_CC1 #4 LE-TIM0_OUT0 #2	CAN0_RX #1 US1_CLK #2 US2_TX #5 LEU0_TX #3 I2C0_SDA #5	DBG_SWCLKTCK BOOT_TX
PF1	BUSCY BUSDX	TIM0_CC1 #4 WTIM0_CC2 #4 LE-TIM0_OUT1 #2	US1_CS #2 US2_RX #5 U0_TX #5 LEU0_RX #3 I2C0_SCL #5	PRS_CH4 #2 DBG_SWDIOTMS GPIO_EM4WU3 BOOT_RX
PF2	BUSDY BUSCX LCD_SEG0	TIM0_CC2 #4 TIM1_CC0 #5	CAN0_TX #1 US1_TX #5 US2_CLK #5 U0_RX #5 LEU0_TX #4 I2C1_SCL #4	CMU_CLK0 #4 PRS_CH0 #3 ACMP1_O #0 DBG_TDO GPIO_EM4WU4
PF3	BUSCY BUSDX LCD_SEG1	TIM0_CDTI0 #2 TIM1_CC1 #5	US1_CTS #2	CMU_CLK1 #4 PRS_CH0 #1
PF4	BUSDY BUSCX LCD_SEG2	TIM0_CDTI1 #2 TIM1_CC2 #5	US1_RTS #2	PRS_CH1 #1
PF5	BUSCY BUSDX LCD_SEG3	TIM0_CDTI2 #2 TIM1_CC3 #6	US2_CS #5	PRS_CH2 #1 DBG_TDI
PE8	BUSDY BUSCX LCD_SEG4			PRS_CH3 #1
PE9	BUSCY BUSDX LCD_SEG5			
PE10	BUSDY BUSCX LCD_SEG6	TIM1_CC0 #1 WTIM0_CDTI0 #0	US0_TX #0	PRS_CH2 #2 GPIO_EM4WU9
PE11	BUSCY BUSDX LCD_SEG7	TIM1_CC1 #1 WTIM0_CDTI1 #0	US0_RX #0	LES_ALTEX5 PRS_CH3 #2
PE12	BUSDY BUSCX LCD_SEG8	TIM1_CC2 #1 WTIM0_CDTI2 #0 LE-TIM0_OUT0 #4	US0_RX #3 US0_CLK #0 I2C0_SDA #6	CMU_CLK1 #2 CMU_CLKI0 #6 LES_AL-TEX6 PRS_CH1 #3
PE13	BUSCY BUSDX LCD_SEG9	TIM1_CC3 #1 LE-TIM0_OUT1 #4	US0_TX #3 US0_CS #0 I2C0_SCL #6	LES_ALTEX7 PRS_CH2 #3 ACMP0_O #0 GPIO_EM4WU5
PE14	BUSDY BUSCX LCD_SEG10		US0_CTS #0 LEU0_TX #2	
PE15	BUSCY BUSDX LCD_SEG11		US0_RTS #0 LEU0_RX #2	
PA15	BUSAY BUSBX LCD_SEG12		US2_CLK #3	

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
LES_CH4	0: PC4		LESENSE channel 4.
LES_CH5	0: PC5		LESENSE channel 5.
LES_CH6	0: PC6		LESENSE channel 6.
LES_CH7	0: PC7		LESENSE channel 7.
LES_CH8	0: PC8		LESENSE channel 8.
LES_CH9	0: PC9		LESENSE channel 9.
LES_CH10	0: PC10		LESENSE channel 10.
LES_CH11	0: PC11		LESENSE channel 11.
LES_CH12	0: PC12		LESENSE channel 12.
LES_CH13	0: PC13		LESENSE channel 13.
LES_CH14	0: PC14		LESENSE channel 14.
LES_CH15	0: PC15		LESENSE channel 15.
LETIM0_OUT0	0: PD6 1: PB11 2: PF0 3: PC4	4: PE12 5: PC14 6: PA8	Low Energy Timer LETIM0, output channel 0.

Alternate	LOCATION		
Functionality	0 - 3	4 - 7	Description
WTIM1_CC3	0: PD1 1: PD5 2: PC6	4: PE6	Wide timer 1 Capture Compare input / output channel 3.

Port	Bus	CH31	CH30	CH29	CH28	CH27	CH26	CH25	CH24	CH23	CH22	CH21	CH20	CH19	CH18	CH17	CH16	CH15	CH14	CH13	CH12	CH11	CH10	CH9	CH8	CH7	CH6	CH5	CH4	CH3	CH2	CH1	CH0
VDAC0_OUT1 / OPA1_OUT																																	
APORT1Y	BUSAY			PB13		PB11						PB5		PB3				PA15		PA13				PA9				PA5		PA3		PA1	
APORT2Y	BUSBY		PB14		PB12						PB6		PB4						PA14				PA10				PA6		PA4		PA2		PA0
APORT3Y	BUSCY											PF5		PF3		PF1		PE15		PE13		PE11		PE9		PE7		PE5					
APORT4Y	BUSDY												PF4		PF2		PF0		PE14		PE12		PE10		PE8		PE6		PE4				

7.2 QFN80 PCB Land Pattern

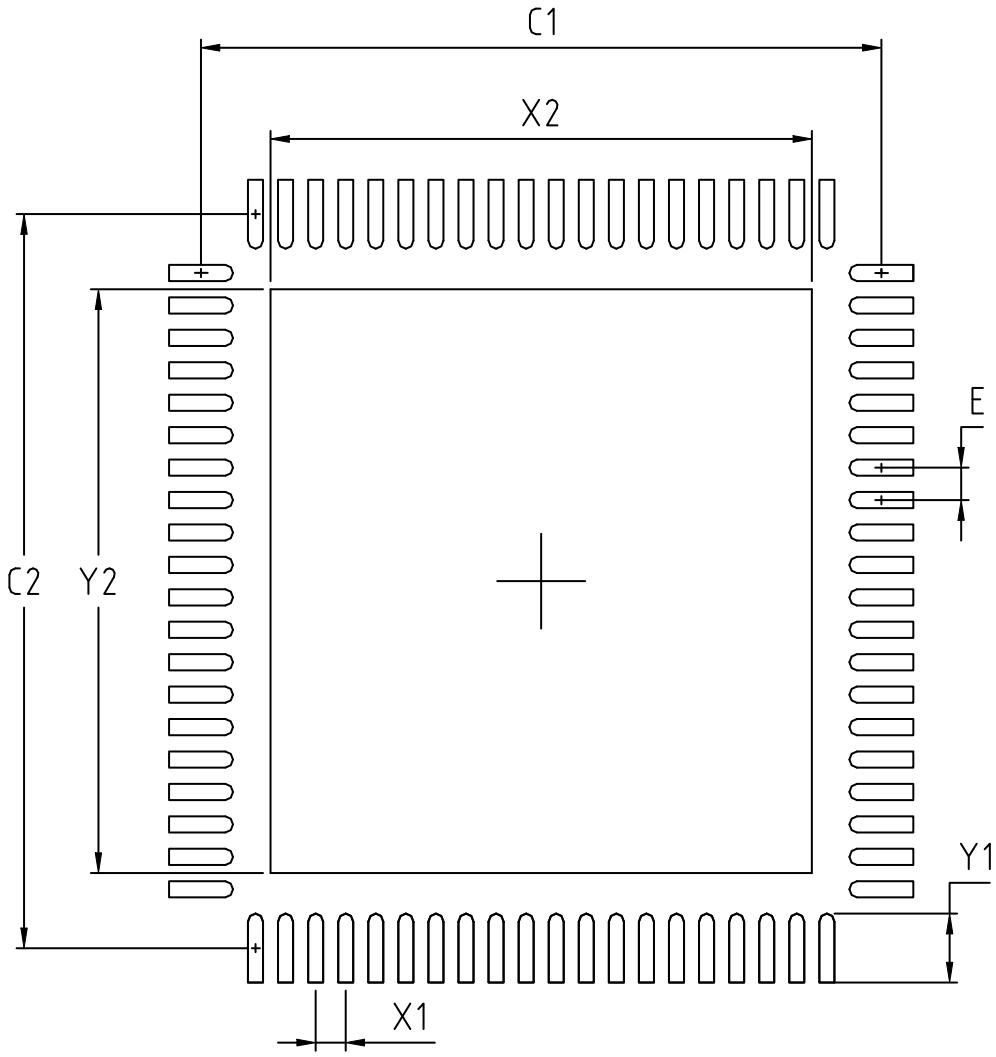

Figure 7.2. QFN80 PCB Land Pattern Drawing

Table 7.2. QFN80 PCB Land Pattern Dimensions

Dimension	Typ
C1	8.90
C2	8.90
E	0.40
X1	0.20
Y1	0.85
X2	7.30
Y2	7.30

Note:

1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. This Land Pattern Design is based on the IPC-7351 guidelines.
3. All dimensions shown are at Maximum Material Condition (MMC). Least Material Condition (LMC) is calculated based on a Fabrication Allowance of 0.05mm.
4. All metal pads are to be non-solder mask defined (NSMD). Clearance between the solder mask and the metal pad is to be 60 µm minimum, all the way around the pad.
5. A stainless steel, laser-cut and electro-polished stencil with trapezoidal walls should be used to assure good solder paste release.
6. The stencil thickness should be 0.125 mm (5 mils).
7. The ratio of stencil aperture to land pad size can be 1:1 for all pads.
8. A 3x3 array of 1.45 mm square openings on a 2.00 mm pitch can be used for the center ground pad.
9. A No-Clean, Type-3 solder paste is recommended.
10. The recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

8. TQFP64 Package Specifications

8.1 TQFP64 Package Dimensions

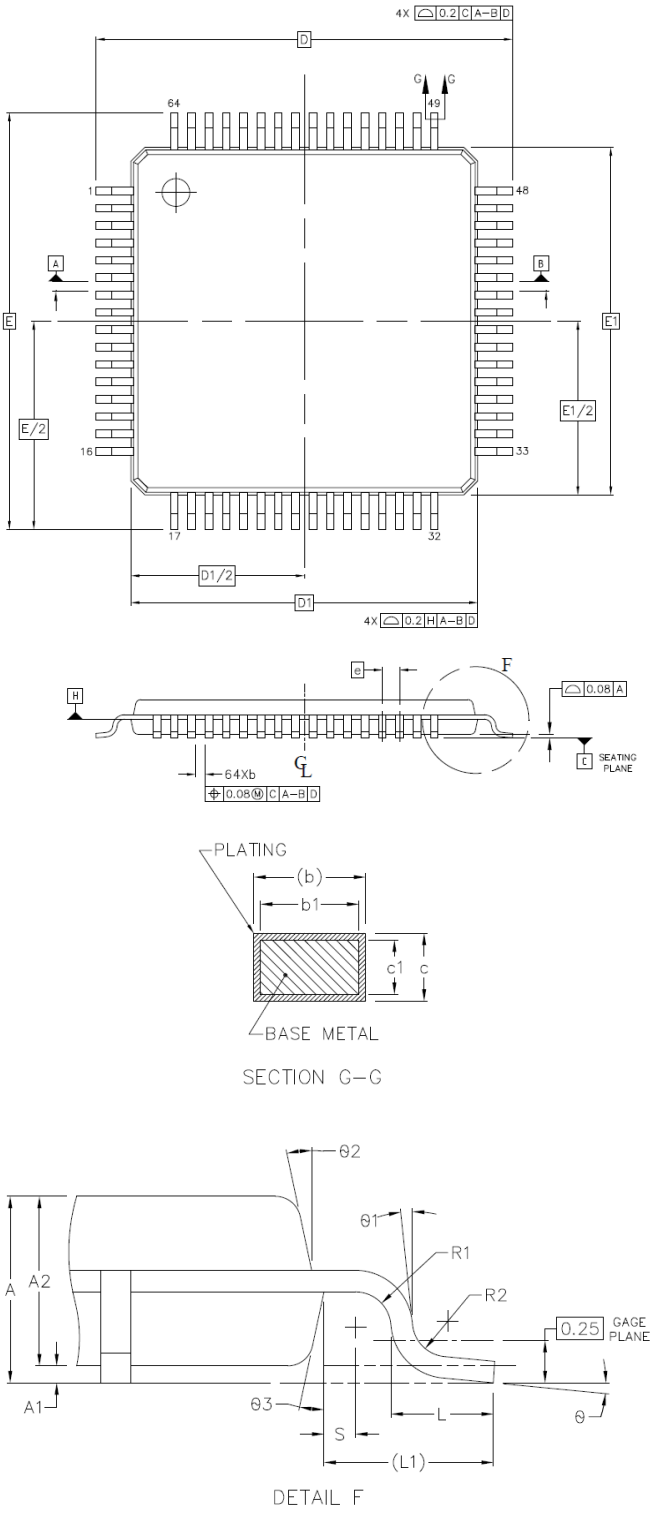

Figure 8.1. TQFP64 Package Drawing

Table 9.1. QFN64 Package Dimensions

Dimension	Min	Typ	Max
A	0.70	0.75	0.80
A1	0.00	—	0.05
b	0.20	0.25	0.30
A3	0.203 REF		
D	9.00 BSC		
e	0.50 BSC		
E	9.00 BSC		
D2	7.10	7.20	7.30
E2	7.10	7.20	7.30
L	0.40	0.45	0.50
L1	0.00	—	0.10
aaa	0.10		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		

Note:
1. All dimensions shown are in millimeters (mm) unless otherwise noted.
2. Dimensioning and Tolerancing per ANSI Y14.5M-1994.
3. Recommended card reflow profile is per the JEDEC/IPC J-STD-020 specification for Small Body Components.

11.3 QFN32 Package Marking

Figure 11.3. QFN32 Package Marking

The package marking consists of:

- PPPPPPPPPP – The part number designation.
- TTTTTT – A trace or manufacturing code. The first letter is the device revision.
- YY – The last 2 digits of the assembly year.
- WW – The 2-digit workweek when the device was assembled.